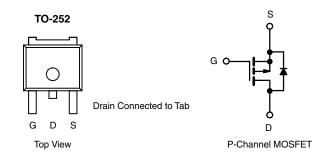


Vishay Siliconix

Automotive P-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	- 30			
$R_{DS(on)}(\Omega)$ at V_{GS} = - 10 V	0.007			
$R_{DS(on)}(\Omega)$ at V_{GS} = - 4.5 V	0.011			
I _D (A)	- 50			
Configuration	Single			



FEATURES

- TrenchFET[®] Power MOSFET
- AEC-Q101 Qualified^d
- 100 % R_g and UIS Tested
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



HALOGEN

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50P03-07-GE3

ABSOLUTE MAXIMUM RATINGS (T	_C = 25 °C, unles	s otherwise noted	ł)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	- 30	M	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current ^a	T _C = 25 °C	1	- 50		
	T _C = 125 °C	I _D	- 50		
Continuous Source Current (Diode Conduction) ^a		I _S	- 50	А	
Pulsed Drain Current ^b		I _{DM}	- 200		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 50		
Single Pulse Avalanche Energy		E _{AS}	125	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	136	w	
	T _C = 125 °C	P _D	45		
Operating Junction and Storage Temperature Rar	nge	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	50	°C/W	
Junction-to-Case (Drain)		R _{thJC}	1.1	0/10	

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	V _{GS} = 0, I _D = - 250 μA		-	-	v
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = - 250 μA	- 1.5	- 2.0	- 2.5	v
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA
Zero Gate Voltage Drain Current		$V_{GS} = 0 V$	V _{DS} = - 30 V	-	-	- 1	
	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = -30 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	- 50	μA
		$V_{GS} = 0 V$	$V_{DS} = -30 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	- 250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	$V_{DS} \le -5 V$	- 50	-	-	Α
Drain-Source On-State Resistance ^a		V _{GS} = - 10 V	I _D = - 20 A	-	0.005	0.007	
	P	V _{GS} = - 10 V	I _D = - 20 A, T _J = 125 °C	-	-	0.011	
	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 20 A, T _J = 175 °C	-	-	0.012	Ω
		$V_{GS} = -4.5 V$	I _D = - 15 A	-	0.008	0.011	
Forward Transconductanceb	9 _{fs}	V _{DS} =	- 15 V, I _D = - 20 A	-	52	-	S
Dynamic ^b	•						
Input Capacitance	C _{iss}			-	4390	5490	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 0 V$ $V_{DS} = -25 V, f = 1 MHz$	-	766	960	pF
Reverse Transfer Capacitance	C _{rss}			-	672	840	
Total Gate Charge ^c	Qg			-	97	146	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -15 \text{ V}, I_D = -75 \text{ A}$	-	7.6	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	29.1	-	
Gate Resistance	Rg	f = 1 MHz		1.40	2.85	4.50	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	11	17	
Rise Time ^c	t _r	V_{DD} = - 15 V, R _L = 0.2 Ω I _D \cong - 75 A, V _{GEN} = - 10 V, R _g = 1 Ω		-	12	18	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	63	95	
Fall Time ^c	t _f			-	28	42	
Source-Drain Diode Ratings and Char	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	- 200	Α
Forward Voltage	V _{SD}	$I_{\rm F} = -30$ A, $V_{\rm GS} = 0$		-	- 0.85	- 1.5	V

Notes

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

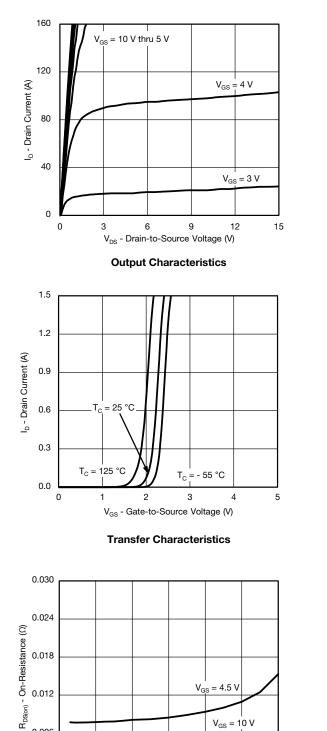
c. Independent of operating temperature.

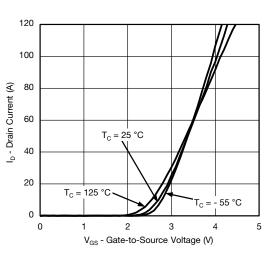
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



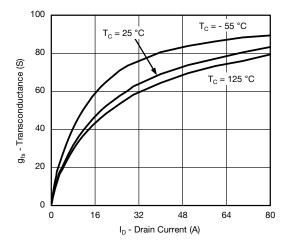
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

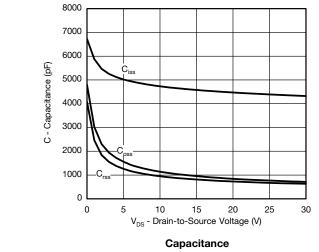




Transfer Characteristics



Transconductance



S12-1848-Rev. B, 30-Jul-12

20

40

60

I_D - Drain Current (A) **On-Resistance vs. Drain Current**

80

100

120

0.006

0.000

0

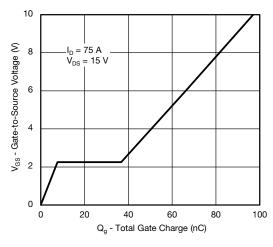
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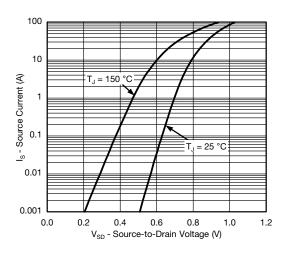


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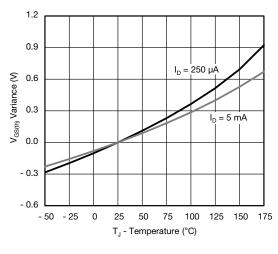
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



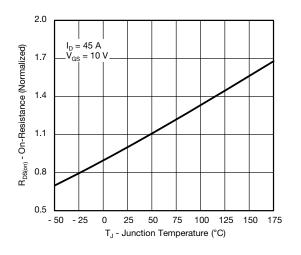
Gate Charge



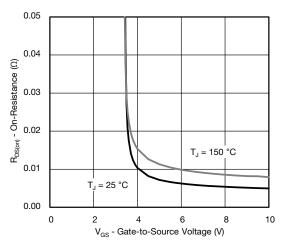
Source Drain Diode Forward Voltage



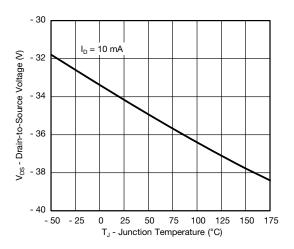
Threshold Voltage



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

S12-1848-Rev. B, 30-Jul-12

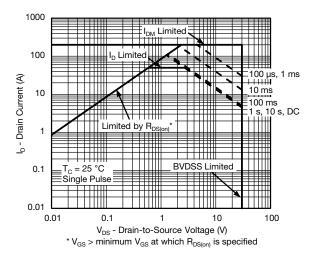
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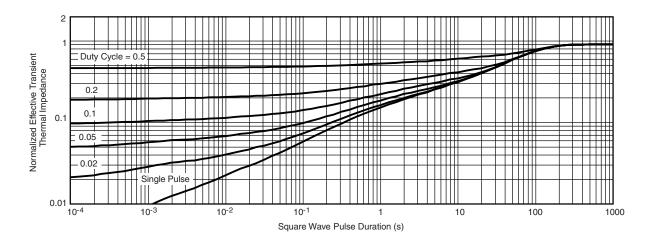


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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area

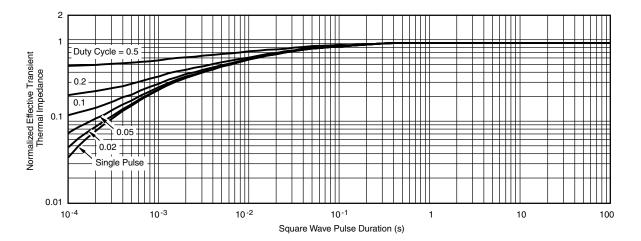


Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

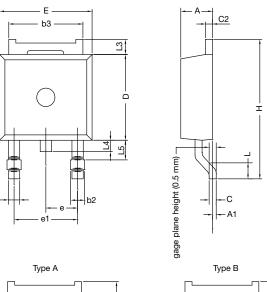
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

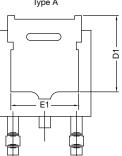
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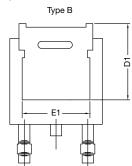


TO-252AA Case Outline





b



DIM.	MILLIN	METERS	INCHES	
	MIN.	MAX.	MIN.	MAX.
А	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
С	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
Н	9.40	10.41	0.370	0.410
е	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060

Notes

• Dimension L3 is for reference only

• Dimension D1 and E1 on type A and B is the same

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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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Revision: 01-Jan-2025

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